



YAO-3950

PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Yoshihisa Nagano et al.

: Art Unit: 2815

Serial No.: 09/103,873

: Examiner: J. Diaz

Filed: June 24, 1998

For: SEMICONDUCTOR DEVICE AND
METHOD FOR FABRICATING THE SAME

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AMENDMENT

COPY

1 Assistant Commissioner for Patents
2 Washington, DC 20231

3 SIR:

4 Responsive to the Official Action dated April 9, 2002, please amend
5 the above-identified application as follows:

6 CLAIMS:

7 Please replace claims 1, 30 and 31 with the following amended
8 claims:

9 1. (As Amended) A semiconductor device, comprising:

10 a capacitor provided on a supporting substrate having an integrated
11 circuit thereon and including a lower electrode, a dielectric film, and an upper
12 electrode, said dielectric film being formed from either a dielectric material having
13 a high dielectric constant or a ferroelectric material;

14 a first interlayer insulating film provided so as to directly cover the
15 capacitor;

16 a first interconnect selectively provided on the first interlayer
17 insulating film and electrically connected to the integrated circuit and the capacitor
18 through a first contact hole formed in the first interlayer insulating film;

19 a second interlayer insulating film having a tensile stress provided so
20 as to directly cover the first interconnect and the first interlayer insulating film;

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